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FDN304P

P-Channel 1.8V Specified PowerTrench® MOSFET

General Description

This P-Channel 1.8V specified MOSFET uses Fairchild's advanced low voltage PowerTrench process. It has been optimized for battery power management applications.

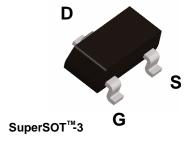
Applications

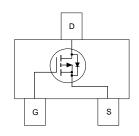
- · Battery management
- Load switch
- · Battery protection

Features

• -2.4 A, -20 V.
$$\begin{split} R_{DS(ON)} &= 52 \text{ m}\Omega \,\, @ \,\, V_{GS} = -4.5 \,\, V \\ R_{DS(ON)} &= 70 \,\, \text{m}\Omega \,\, @ \,\, V_{GS} = -2.5 \,\, V \\ R_{DS(ON)} &= 100 \,\, \text{m}\Omega \,\, @ \,\, V_{GS} = -1.8 \,\, V \end{split}$$

- · Fast switching speed
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}$
- SuperSOT[™] -3 provides low R_{DS(ON)} and 30% higher power handling capability than SOT23 in the same footprint





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1a)	-2.4	A
	- Pulsed		-10	
P _D	Maximum Power Dissipation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity	
304 FDN304P		7"	8mm	3000 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			ı	ı	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
ΔBV _{DSS} ΔT, _J	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$, Referenced to 25°C		-13		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -8 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.8	-1.5	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		3		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$\begin{array}{cccc} V_{GS} = -4.5 \ V, & I_D = -2.4 \ A \\ V_{GS} = -2.5 \ V, & I_D = -2.0 \ A \\ V_{GS} = -1.8 \ V, & I_D = -1.8 \ A \end{array}$		36 47 65	52 70 100	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-10			Α
g FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -1.25 \text{ A}$		12		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -10 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		1312		pF
Coss	Output Capacitance	f = 1.0 MHz		240		pF
C _{rss}	Reverse Transfer Capacitance			106		pF
Switchin	g Characteristics (Note 2)			•	•	
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, \qquad I_{D} = -1 \text{ A},$		15	27	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		15	27	ns
t _{d(off)}	Turn-Off Delay Time			40	64	ns
t _f	Turn-Off Fall Time			25	40	ns
$\overline{Q_g}$	Total Gate Charge	$V_{DS} = -10 \text{ V}, I_{D} = -2.4 \text{ A},$		12	20	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 \text{ V}$		2		nC
Q _{gd}	Gate-Drain Charge	1		2		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings		•	•	•
I _s	Maximum Continuous Drain–Source				-0.42	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -0.42 \text{(Note 2)}$		-0.6	-1.2	V

Notes:

^{1.} $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 250°C/W when mounted on a 0.02 in² pad of 2 oz. copper.

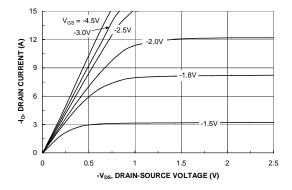


b) 270°C/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics



Pain Davin Current (a)

-1.8V

-2.5V

-3.0V

-4.5V

-3.0V

-4.5V

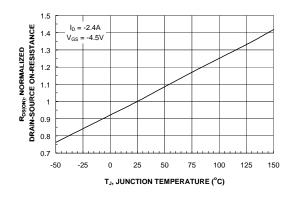
-4.5V

-4.5V

-4.5V

Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



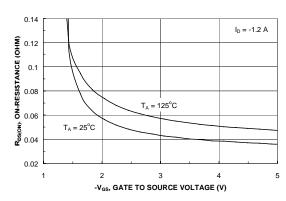
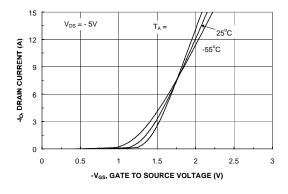


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



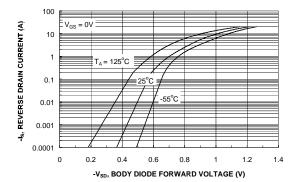
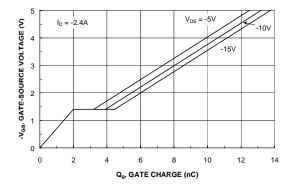


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



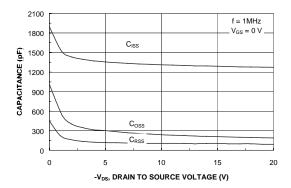
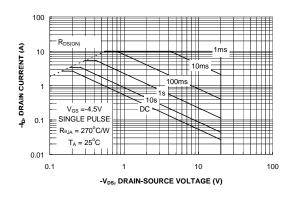


Figure 7. Gate Charge Characteristics.





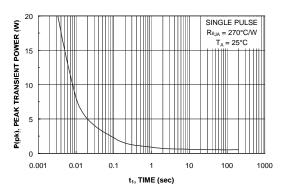


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

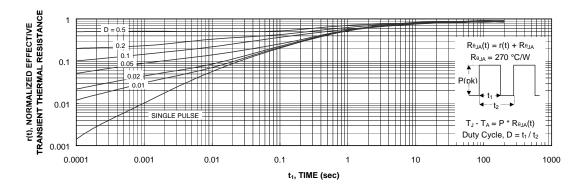


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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